



PRODUCT DATA SHEET



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Datasheet



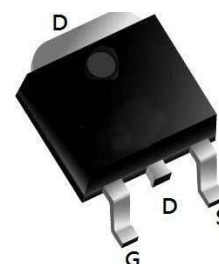
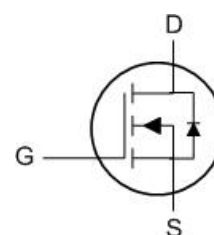
Resources



Samples

Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to JINGAO_questions@jgsemi.com.

- ★ Super Low Gate Charge
- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology


TO252-3L


Absolute Maximum Ratings

Symbol	Parameter	Rating		Units
		10s	Steady State	
V_{DS}	Drain-Source Voltage	30		V
V_{GS}	Gate-Source Voltage	± 20		V
$I_D@T_C=25^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^1$	80		A
$I_D@T_C=75^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^1$	63		A
I_{DM}	Pulsed Drain Current ²	360		A
EAS	Single Pulse Avalanche Energy ³	169		mJ
I_{AS}	Avalanche Current	36		A
$P_D@T_C=25^{\circ}C$	Total Power Dissipation ⁴	71		W
T_{STG}	Storage Temperature Range	-55 to 175		$^{\circ}C$
T_J	Operating Junction Temperature Range	-55 to 175		$^{\circ}C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	2.1	$^{\circ}C/W$

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	30	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =1mA	---	---	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =20A	---	4.2	5.9	mΩ
		V _{GS} =4.5V, I _D =15A	---	6.3	9.7	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.2	1.5	2.5	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	---	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =30V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =30V, V _{GS} =0V, T _J =100°C	---	---	100	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =30A	---	24	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	1.6	---	Ω
Q _g	Total Gate Charge	V _{GS} =10V, V _{DS} =15V, I _D =20A	---	34	---	nC
Q _{gs}	Gate-Source Charge		---	6.5	---	
Q _{gd}	Gate-Drain Charge		---	7.5	---	
T _{d(on)}	Turn-On Delay Time	V _{GS} =10V, V _{DS} =15V, R _L =0.75Ω, R _{GEN} =6Ω	---	7	---	ns
T _r	Rise Time		---	14	---	
T _{d(off)}	Turn-Off Delay Time		---	34	---	
T _f	Fall Time		---	11	---	
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	1760	---	pF
C _{oss}	Output Capacitance		---	193	---	
C _{rss}	Reverse Transfer Capacitance		---	172	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,5}	V _G =V _D =0V, Force Current	---	---	80	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V

Note :

1 The data is tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.

2 The data is tested by pulsed pulse width is 300us duty cycle is 2%

3 The EAS data shows Max. Rating The test condition is V_{DS}=30V, V_{GS}=10V, R_g=25Ω, L=0.5mH.

4 The power dissipation is limited by 50°C junction temperature

5 The data is theoretically the same as I_{DS(on)} and I_{DDM} in real applications should be limited by total power dissipation.

Typical Electrical and Thermal Characteristics (Curves)

Figure 1. Output Characteristics

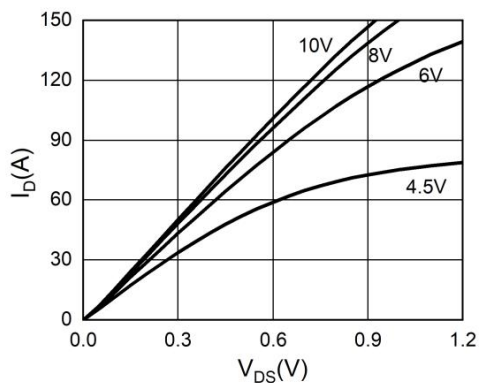


Figure 2. Transfer Characteristics

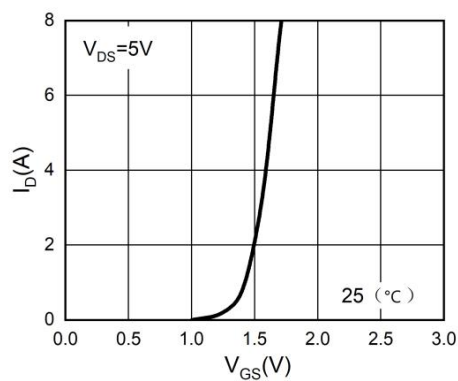


Figure 3. Power Dissipation

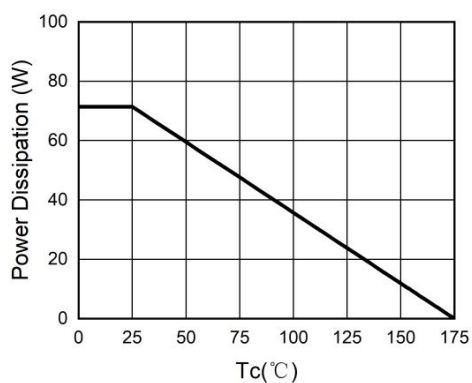


Figure 4. Drain Current

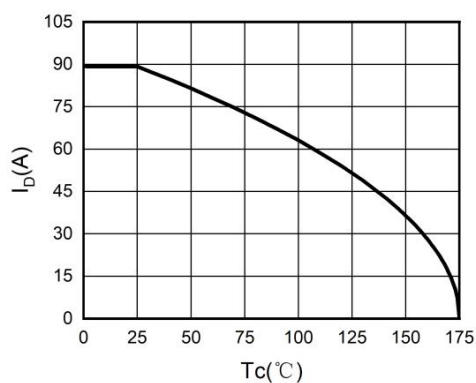


Figure 5. BV_{DSS} vs Junction Temperature

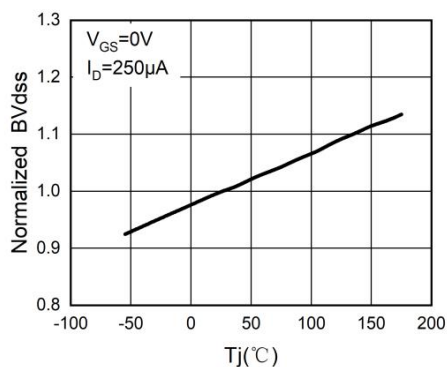


Figure 6. $R_{DS(ON)}$ vs Junction Temperature

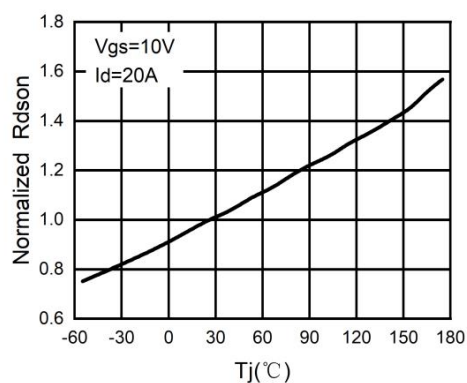
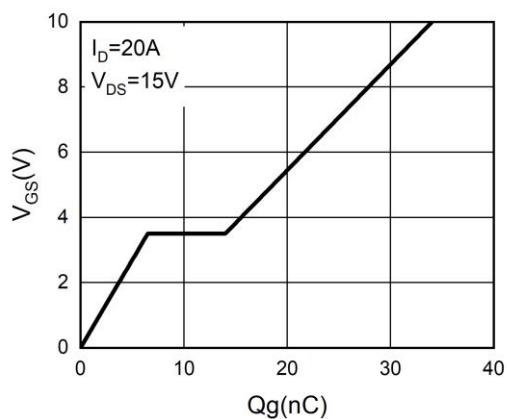
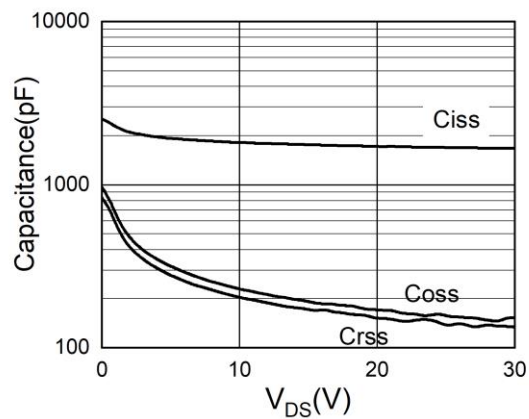
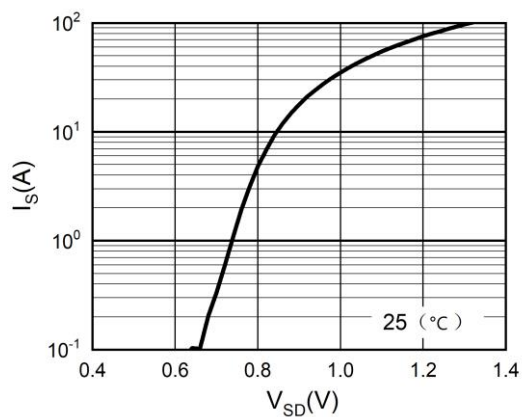
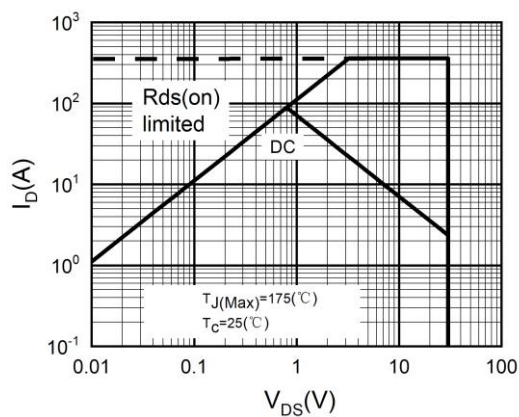
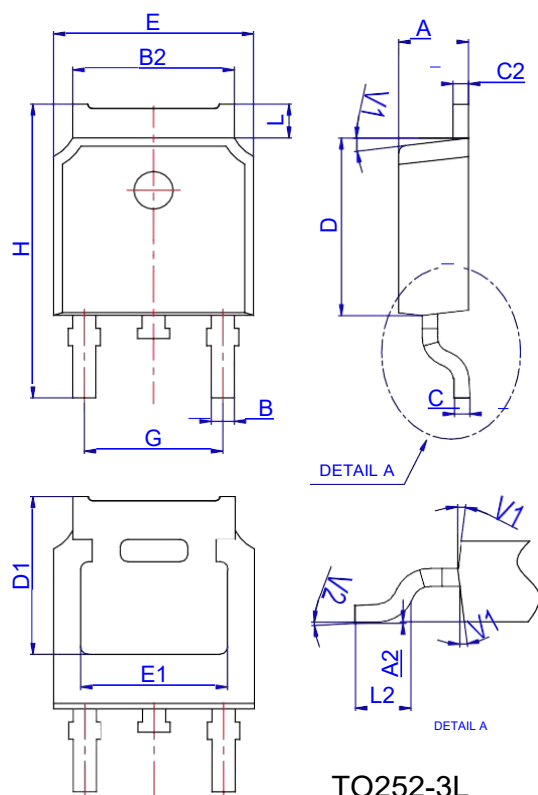


Figure 7. Gate Charge Waveforms

Figure 8. Capacitance

Figure 9. Body-Diode Characteristics

Figure 10. Maximum Safe Operating Area


Package Mechanical Data TO252-3L



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

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